



## ZXTN25100DG

### 100V NPN high gain transistor in SOT223

#### Summary

$BV_{CEX} > 180V$

$BV_{CEO} > 100V$

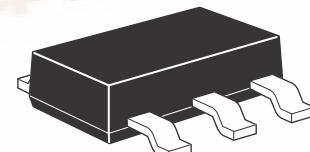
$BV_{ECO} > 6V$

$I_C(\text{cont}) = 3A$

$V_{CE(\text{sat})} < 100mV @ 1A$

$R_{CE(\text{sat})} = 85m\Omega$

$P_D = 3.0W$



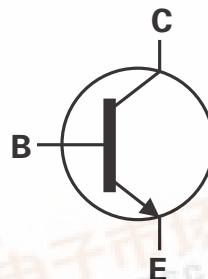
Complementary part number ZXTP19100CG

#### Description

Packaged in the SOT223 outline this new low saturation NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

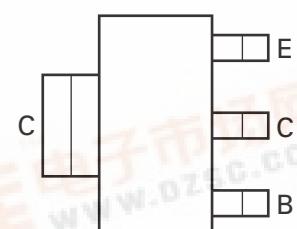
#### Features

- High power dissipation SOT223 package
- High gain
- Low saturation voltage
- 180V forward blocking voltage
- 6V reverse blocking voltage



#### Applications

- PSU start up circuit
- DC - DC converters
- Motor drive
- Relay, lamp and solenoid drive



Pinout - top view

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25100DGTA	7	12	1000

#### Device marking

- ZXTN25  
100D

# ZXTN25100DG

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	$V_{CBO}$	180	V
Collector-Emitter voltage (forward blocking)	$V_{CEX}$	180	V
Collector-Emitter voltage	$V_{CEO}$	100	V
Emitter-Collector voltage (reverse blocking)	$V_{ECO}$	6	V
Emitter-Base voltage	$V_{EBO}$	7	V
Continuous Collector current <sup>(c)</sup>	$I_C$	3	A
Base current	$I_B$	1	A
Peak pulse current	$I_{CM}$	3.5	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup>	$P_D$	1.2	W
Linear derating factor		9.6	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup>	$P_D$	1.6	W
Linear derating factor		12.8	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(c)</sup>	$P_D$	3	W
Linear derating factor		24	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup>	$P_D$	5.3	W
Linear derating factor		42	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_C = 25^\circ\text{C}$ <sup>(e)</sup>	$P_D$	7.3	W
Linear derating factor		58	$\text{mW}/^\circ\text{C}$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	°C

## Thermal resistance

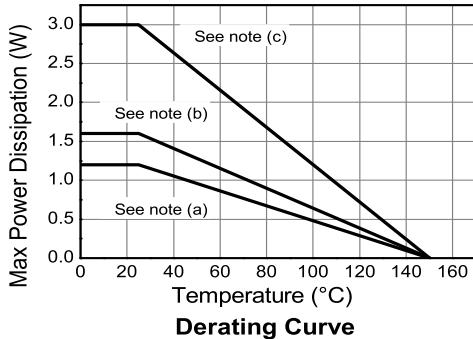
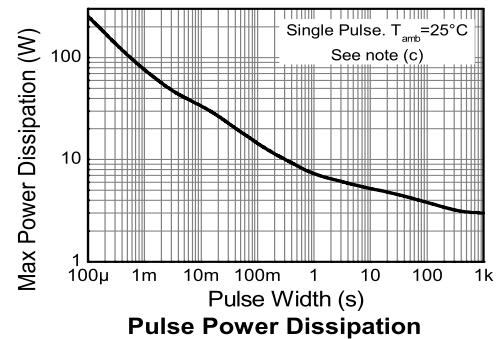
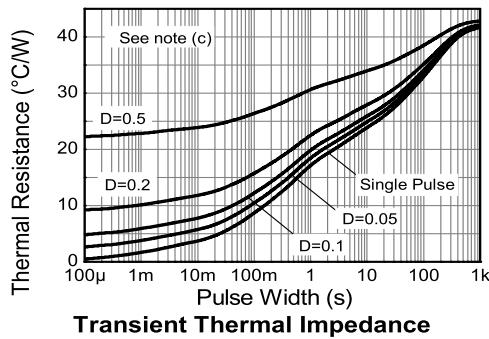
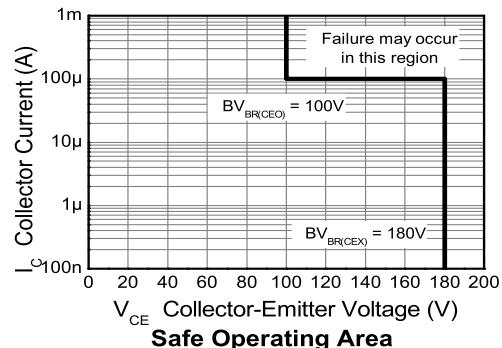
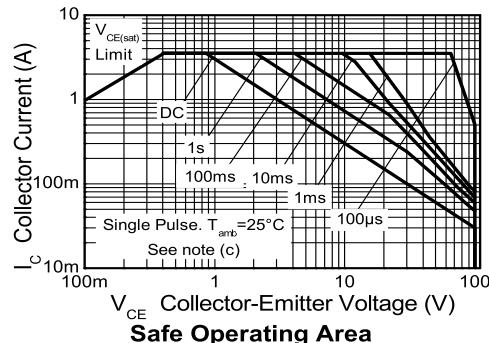
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	104	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	78	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	42	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	23.5	°C/W
Junction to case <sup>(e)</sup>	$R_{\Theta JC}$	16	°C/W

### NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at  $t < 5$  seconds.
- (e) Junction to case (collector tab). Typical

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## Thermal characteristics



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## Electrical characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

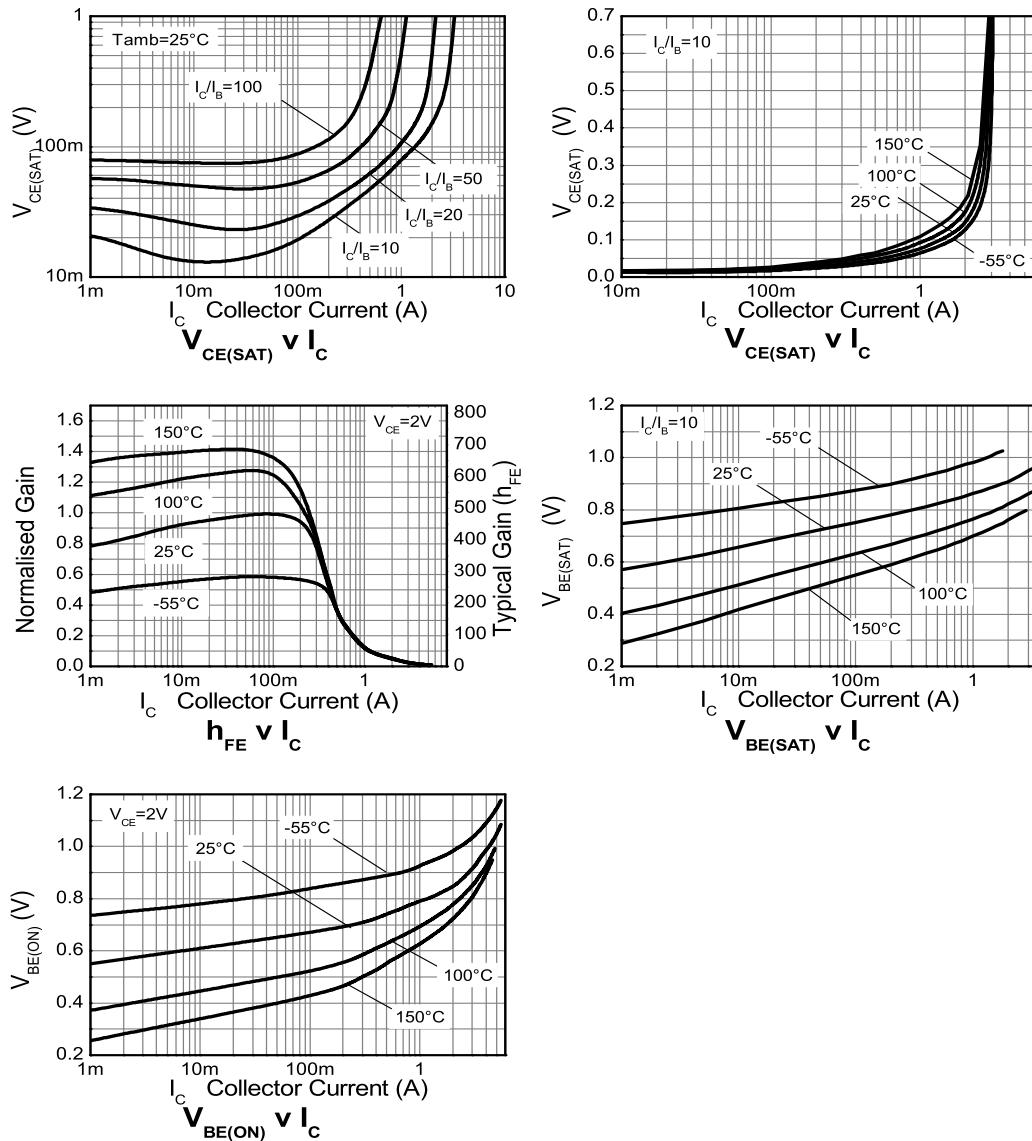
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	$BV_{CBO}$	180	220		V	$I_C = 100\mu A$
Collector-Emitter breakdown voltage (forward blocking)	$BV_{CEX}$	180	220		V	$I_C = 100\mu A, R_{BE} < 1k\Omega$ or $-1V < V_{BC} < 0.25V$
Collector-Emitter breakdown voltage	$BV_{CEO}$	100	130		V	$I_C = 10mA$ (*)
Emitter-Collector breakdown voltage (reverse blocking)	$BV_{ECX}$	6	8.2		V	$I_E = 100\mu A, R_{BC} < 1k\Omega$ or $0.25V > V_{BC} > -0.25V$
Emitter-Collector breakdown voltage (reverse blocking)	$BV_{ECO}$	6	8.7		V	$I_E = 100\mu A$
Emitter-Base breakdown voltage	$BV_{EBO}$	7	8.3		V	$I_E = 100\mu A$
Collector-Base cut-off current	$I_{CBO}$		<1	50 0.5	nA $\mu A$	$V_{CB} = 180V$ $V_{CB} = 180V, T_{amb} = 100^\circ C$
Collector-Emitter cut-off current	$I_{CEX}$			100	nA	$V_{CE} = 100V, R_{BE} < 1k\Omega$ or $-1V < V_{BE} < 0.25V$
Emitter-Base cut-off current	$I_{EBO}$		<1	50	nA	$V_{EB} = 5.6V$
Collector-Emitter saturation voltage	$V_{CE(sat)}$		120 80 215 200	170 100 345 500	mV mV mV mV	$I_C = 0.5A, I_B = 10mA$ (*) $I_C = 1A, I_B = 100mA$ (*) $I_C = 2.5A, I_B = 250mA$ (*) $I_C = 3A, I_B = 600mA$ (*)
Base-Emitter saturation voltage	$V_{BE(sat)}$		1020	1100	mV	$I_C = 3A, I_B = 600mA$ (*)
Base-Emitter turn-on voltage	$V_{BE(on)}$		905	1000	mV	$I_C = 3A, V_{CE} = 2V$ (*)
Static forward current transfer ratio	$h_{FE}$	300 120 40	450 170 60 10	900		$I_C = 10mA, V_{CE} = 2V$ (*) $I_C = 0.5A, V_{CE} = 2V$ (*) $I_C = 1A, V_{CE} = 2V$ (*) $I_C = 3A, V_{CE} = 2V$ (*)
Transition frequency	$f_T$		175		MHz	$I_C = 50mA, V_{CE} = 10V$ $f = 100MHz$
Input capacitance	$C_{ibo}$		154	250	pF	$V_{EB} = 0.5V, f = 1MHz$ (*)
Output capacitance	$C_{obo}$		8.7	15	pF	$V_{CB} = 10V, f = 1MHz$ (*)
Delay time	$t_d$		16.4		ns	$I_C = 500mA, V_{CC} = 10V$ , $I_{B1} = -I_{B2} = 50mA$
Rise time	$t_r$		115		ns	
Storage time	$t_s$		763		ns	
Fall time	$t_f$		158		ns	

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

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## Typical characteristics

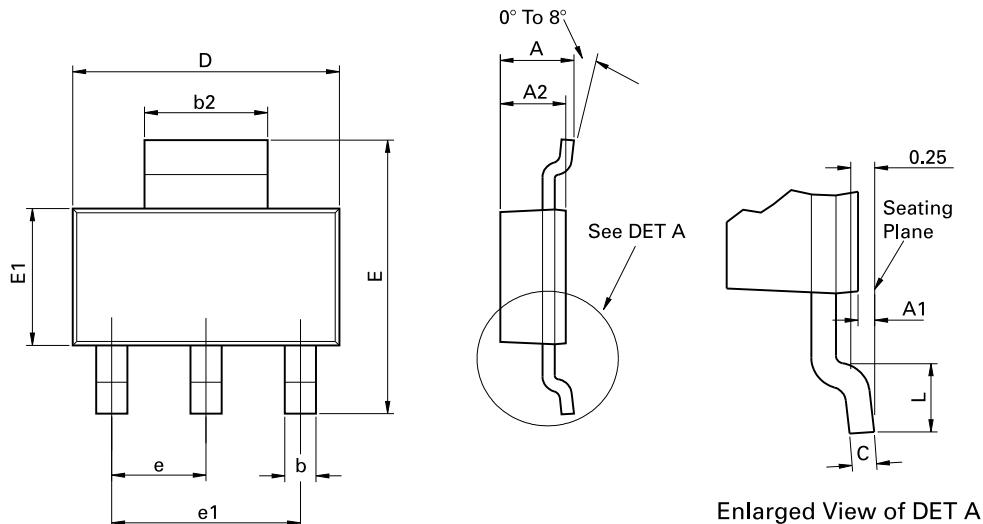


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## Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	e	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

# ZXTN25100DG

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